



ATTORNEY DOCKET NO.: LOTFI 22-2

2811
#23/Req.
for
PATENT
Regon.
9/11/03
RECEIVED
TC 2600 MAIL ROOM
John Th

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ashraf W. Lotfi, *et al.*

Serial No.: 09/448,856

Filed: November 23, 1999

Title: SiC NMOSFET FOR USE AS A POWER SWITCH AND
A METHOD OF MANUFACTURING THE SAME

Group: 2811

Examiner: Ori Nadav

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service as
first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313, on
5-29-03 (Date)
Elizabeth Schumacher
(Printed or typed name of person signing the certificate)
Elizabeth Schumacher
(Signature of the person signing the certificate)

Sir:

REQUEST FOR RECONSIDERATION UNDER 37 C.F.R. § 1.111

In response to the Examiner's Action mailed May 30, 2003, please reconsider the above-
identified application for the following reasons.

IN THE CLAIMS:

Claims 1-43 were previously canceled without prejudice or disclaimer.

44. (Previously Presented) A semiconductor device, comprising:

a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:

a silicon carbide tub located within a trench formed in a conductive substrate;